

## NIR/Red Enhanced 6 mm<sup>2</sup> Photodiode-Preamplifier



## **FEATURES**

- Large Active Area
- Low Noise
- High Sensitivity
- Custom Gains Available
- Hermetically Sealed TO-39

### **Electro-Optical Characteristics at 23°C**

Parameters	Test Conditions	Min	Тур	Max	Units
Active Area	3.30 mm x 1.78 mm		5.87		mm <sup>2</sup>
Dark Offset	$V_s = \pm 5 V$		1	±2	mV
Dark Offset Noise	V <sub>s</sub> = ±5 BW = 0.1 to 135 kHz		283	500	μV rms
Sensitivity	$V_s = \pm 5 V$ $\lambda = 940 \text{ nm}$	275	315		V/µW
Frequency Response (-3 db)	$V_s = \pm 5 V$	100	130		Hz
NEP	λ = 940 nm		1.2		fW/√Hz
Transimpedance Gain			500		MΩ
Supply Current			850	950	μA

#### **Absolute Ratings**

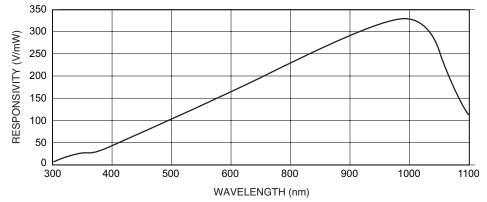
Parameters	Units		
Voltage Supply Range +V to –V*	5 to 15 V		
Power Dissipation	15 mW		
Storage and Operating Temperature	–25 to + 100°C		
Soldering Temperature (1/16" from case for 3 seconds max)	+260°C		

\*Voltage supply across the device requires a minimum of 5 V to a maximum of 15 V from +V to -V.

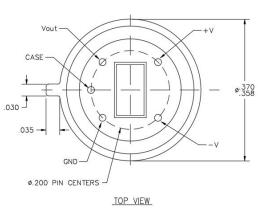


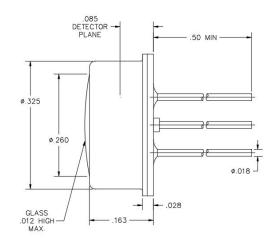
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**Typical Spectral Response** 



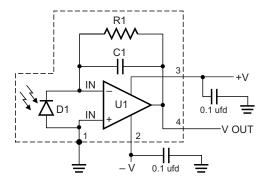
### **Package Information**





ALL DIMENSIONS ARE IN INCH UNITS

#### Dimensions are in inch [metric] units.



Specifications are subject to change without prior notice.